

**AMENDMENTS TO CLAIMS**

1. (Cancelled)

2. (Currently Amended) A semiconductor wafer protection structure, comprising a circular semiconductor wafer and a circular laminated protective sheet overlaid on a circuit surface of the circular semiconductor wafer, whereby said circular laminated protective sheet prevents vibration and damage to the wafer during backgrinding and transportation,

wherein the circular laminated protective sheet comprises a first circular protective layer having substantially the same size as an outer diameter of the circular semiconductor wafer and a second circular protective layer laminated on the first circular protective layer and having an outer diameter that is equal to or larger than the outer diameter of the first circular protective layer, and the circular laminated protective sheet is overlaid on the circuit surface via the side of the first circular protective layer, and

the first circular protective layer includes a film having a stress relaxation rate of at least 40% after 1 minute of 10% elongation, and the second circular protective layer includes a film having a value of Young's modulus x thickness of at least  $5.0 \times 10^4$  N/m.

3. (Cancelled)

4. (Previously Presented) The semiconductor wafer protection structure according to claim 2, wherein the first circular protective layer has an outer diameter that is smaller than the outer diameter of the circular semiconductor wafer by -2.0 to 0mm and the second circular protective layer has an outer diameter that is larger than the outer diameter of the circular semiconductor wafer by +0.1 to +2.0mm.

5-10. (Cancelled)

11. (Currently Amended) A laminated protective sheet for a circular semiconductor wafer comprising a first circular protective layer and a second circular protective layer, whereby said circular laminated protective sheet prevents vibration and damage to the wafer during backgrinding and transportation,

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wherein the second circular protective layer has a larger outer diameter than that of the first circular protective layer, and

the first circular protective layer includes a film having a stress relaxation rate of at least 40% after 1 minute of 10% elongation, and the second circular protective layer includes a film having a value of Young's modulus x thickness of at least  $5.0 \times 10^4$  N/m.

12. (Previously Presented) The laminated protective sheet for a circular semiconductor wafer according to claim 11, wherein the second circular protective layer has an outer diameter that is larger than the outer diameter of the first circular protective layer by +0.1 to +4.0 mm.

13-15. (Cancelled)

16. (Previously Presented) The semiconductor wafer protection structure according to claim 2, wherein the circular laminated protective sheet has a maximum diameter that is larger than the outer diameter of the circular semiconductor wafer by +0.1 to 10 mm.

17-20. (Cancelled)